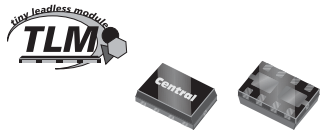
CTLDM8120-M832D

SURFACE MOUNT
DUAL, P-CHANNEL
ENHANCEMENT-MODE
SILICON MOSFETS



Top View Bottom View

TLM832D CASE

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DESCRIPTION:

The CENTRAL SEMICONDUCTOR CTLDM8120-M832D is an Enhancement-mode Dual P-Channel Field Effect Transistor, manufactured by the P-Channel DMOS Process, designed for high speed pulsed amplifier and driver applications. This MOSFET offers Low $r_{DS(ON)}$ and Low Threshold Voltage.

MARKING CODE: CFV

- Device is ***Halogen Free*** by design

APPLICATIONS:

- Switching Circuits
- DC - DC Converters
- Battery powered portable devices

FEATURES:

- ESD protection up to 2kV
- Low $r_{DS(ON)}$ (0.24Ω MAX @ V_{GS}=1.8V)
- High current (I_D=0.95A)
- Logic level compatibility

MAXIMUM RATINGS: (T_A=25°C)	**SYMBOL**		**UNITS**
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	8.0	V
Continuous Drain Current (Steady State)	I_D	0.86	A
Continuous Drain Current, t≤5.0s	I_D	0.95	A
Continuous Source Current (Body Diode)	I_S	0.36	A
Maximum Pulsed Drain Current, tp=10μs	I_{DM}	4.0	A
Maximum Pulsed Source Current, tp=10μs	I_{SM}	4.0	A
Power Dissipation (Note 1)	P_D	1.65	W
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +150	°C
Thermal Resistance (Note 1)	Θ_{JA}	76	°C/W

ELECTRICAL CHARACTERISTICS PER TRANSISTOR: (T_A=25°C unless otherwise noted)

SYMBOL	**TEST CONDITIONS**	**MIN**	**TYP**	**MAX**	**UNITS**
I_{GSSF}, I_{GSSR}	V_{GS}=8.0V, V_{DS}=0		1.0	50	nA
I_{DSS}	V_{DS}=20V, V_{GS}=0		5.0	500	nA
BV_{DSS}	V_{GS}=0, I_D=250μA	20	24		V
$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=250μA	0.45	0.76	1.0	V
V_{SD}	V_{GS}=0, I_S=360mA			0.9	V
$r_{DS(ON)}$	V_{GS}=4.5V, I_D=0.95A		0.085	0.150	Ω
$r_{DS(ON)}$	V_{GS}=4.5V, I_D=0.77A		0.085	0.142	Ω
$r_{DS(ON)}$	V_{GS}=2.5V, I_D=0.67A		0.130	0.200	Ω
$r_{DS(ON)}$	V_{GS}=1.8V, I_D=0.2A		0.190	0.240	Ω
$Q_{g(tot)}$	V_{DS}=10V, V_{GS}=4.5V, I_D=1.0A		3.56		nC
Q_{gs}	V_{DS}=10V, V_{GS}=4.5V, I_D=1.0A		0.36		nC
Q_{gd}	V_{DS}=10V, V_{GS}=4.5V, I_D=1.0A		1.52		nC
g_{FS}	V_{DS}=10V, I_D=810mA	2.0			S
C_{rss}	V_{DS}=16V, V_{GS}=0, f=1.0MHz		80		pF
C_{iss}	V_{DS}=16V, V_{GS}=0, f=1.0MHz		200		pF
C_{oss}	V_{DS}=16V, V_{GS}=0, f=1.0MHz		60		pF
t_{on}	V_{DD}=10V, V_{GS}=4.5V, I_D=0.95A, R_G=6.0Ω		20		ns
t_{off}	V_{DD}=10V, V_{GS}=4.5V, I_D=0.95A, R_G=6.0Ω		25		ns

Notes: (1) FR-4 Epoxy PCB with copper mounting pad area of 54mm^2

R2 (2-August 2011)

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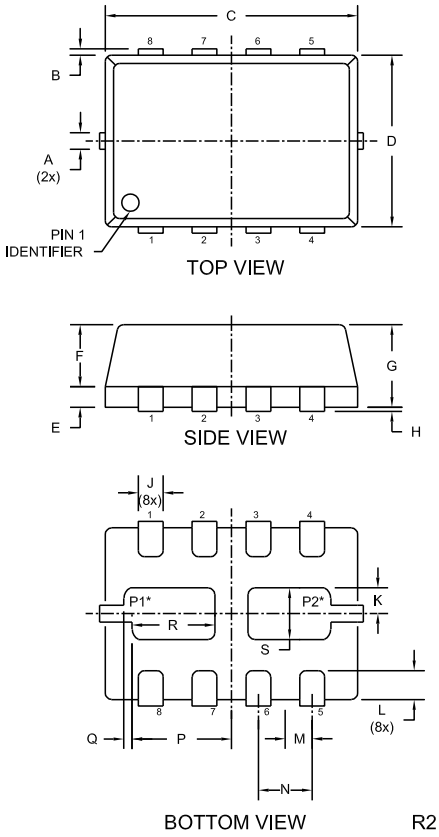
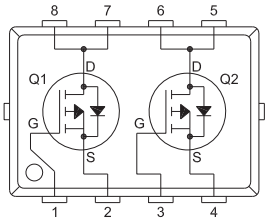
TLM832D CASE - MECHANICAL OUTLINE



DIMENSIONS				
	INCHES		MILLIMETERS	
SYMBOL	MIN	MAX	MIN	MAX
A	0.007	0.012	0.170	0.300
B	-	0.005	-	0.125
C	0.114	0.122	2.900	3.100
D	0.075	0.083	1.900	2.100
E	0.006	0.010	0.150	0.250
F	0.026	0.030	0.650	0.750
G	0.031	0.039	0.800	1.000
H	0.000	0.002	0.000	0.050
J	0.009	0.013	0.240	0.340
K	0.006	0.014	0.160	0.360
L	0.008	0.018	0.200	0.450
M	0.013		0.325	
N	0.026		0.650	
P	0.040	0.048	1.010	1.210
Q	0.004		0.100	
R	0.032	0.040	0.820	1.020
S	0.017	0.025	0.430	0.630

TLM832D (REV: R2)

PIN CONFIGURATION



LEAD CODE:
1) Gate Q1
2) Source Q1
3) Gate Q2
4) Source Q2
5) Drain Q2
6) Drain Q2
7) Drain Q1
8) Drain Q1

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* Note:
- Exposed pad P1 common to pins 7 and 8
- Exposed pad P2 common to pins 5 and 6